

# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	350 280	mA
	t<5s	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	400 310	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I <sub>DM</sub>	1.2	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	359	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	520	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	243	°C/W
Operating and Storage Temperature Range		$T_J,T_STG$	-55 to +150	°C

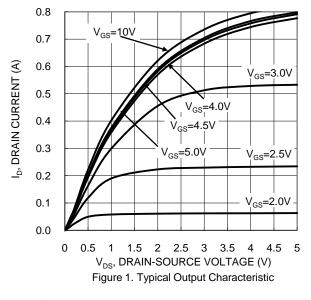
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	- Cyllider		. , , ,	шах	<u> </u>	root containen
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1.0	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>		_	±10.0	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8		1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
		_	_	2.8	Ω	$V_{GS} = 10.0V, I_D = 250mA$
		_	_	3.8		$V_{GS} = 5.0V, I_D = 250mA$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	4.2		$V_{GS} = 4.5V, I_D = 250mA$
		_	_	4.5		$V_{GS} = 4.0V, I_D = 250mA$
				13		$V_{GS} = 2.5V, I_D = 10mA$
Forward Transconductance	g <sub>FS</sub>	80		_	mS	$V_{DS} = 10V, I_D = 0.115A$
Diode Forward Voltage	V <sub>SD</sub>		0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		23.2	_		
Output Capacitance	Coss	_	3.0		pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.2	_		
Gate Resistance	RG	_	79.9		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge V <sub>GS</sub> = 10V	$Q_g$	_	0.9	_		
Total Gate Charge V <sub>GS</sub> = 4.5V	Qg	_	0.4	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$
Gate-Source Charge	Q <sub>gs</sub>	_	0.1	_	nc	I <sub>D</sub> = 150mA
Gate-Drain Charge	$Q_{gd}$	_	0.2	_		
Turn-On Delay Time	t <sub>D(ON)</sub>		2.3	_		
Turn-On Rise Time	t <sub>R</sub>		3.9	_		$V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	11.4	_	ns	$R_{GEN} = 25\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	16.7			

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





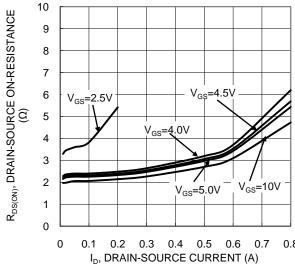
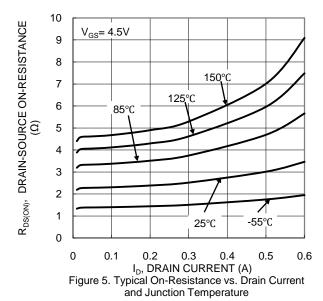
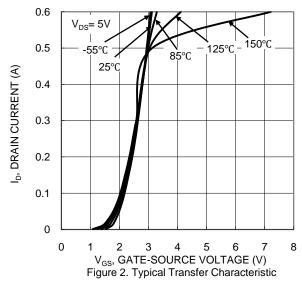
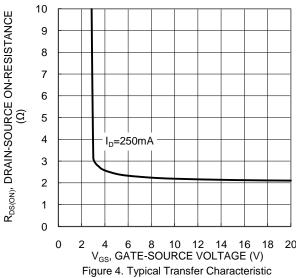


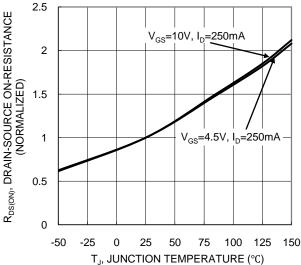
Figure 3. Typical On-Resistance vs. Drain Current

and Gate Voltage









T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction Temperature



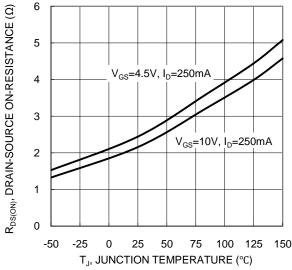
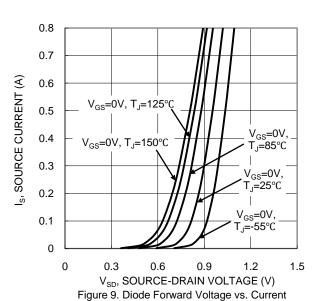


Figure 7. On-Resistance Variation with Junction Temperature



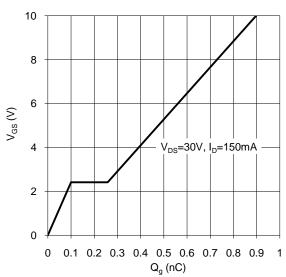
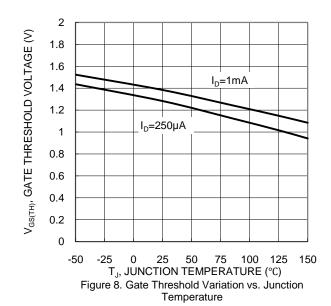
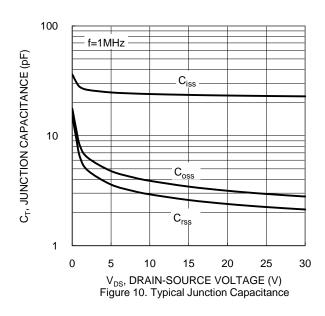


Figure 11. Gate Charge





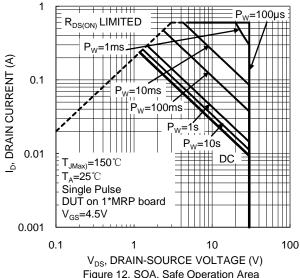


Figure 12. SOA, Safe Operation Area



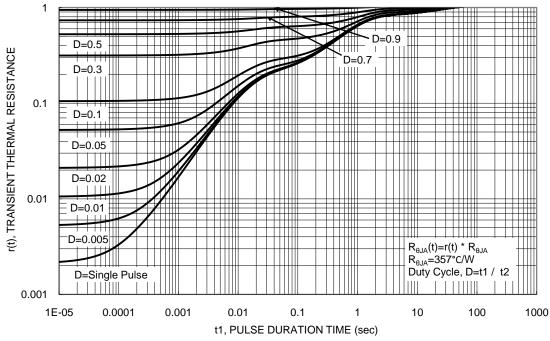
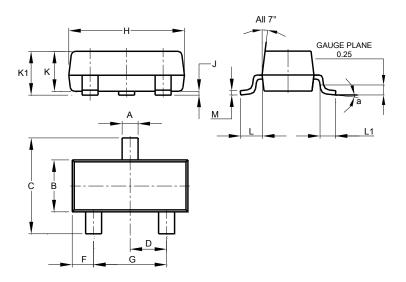


Figure 13. Transient Thermal Resistance

## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

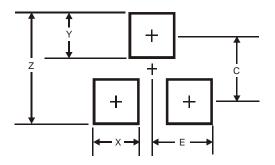


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Ŧ	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
٦	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	a 8°					
All Dimensions in mm						



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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